arXiv:cond-mat/0101277v1 [cond-mat.supr-con] 18 Jan 2001

Influence of impurity scattering on tunneling conductance in normal metal– d -wave superconductor junctions

Y. Tanaka and Y. Tanuma

Department of Applied Physics, Nagoya University and CREST of the Japan Science and Technology Corporation (JST), Nagoya, 464-8603, Japan.

S. Kashiwaya

Electrotechnical Laboratory and CREST of the Japan Science and Technology Corporation (JST), Umezono, Tsukuba, Ibaraki 305-8568, Japan.

(February 1, 2008)

Abstract

Tunneling conductance spectra between a normal metal / d-wave superconductor junction under the presence of bulk impurities in the superconductor are studied. The quasiclassical theory has been applied to calculate the spatial variation of the pair potential and the effect of impurity scattering has been introduced by t-matrix approximation. The magnitude of a subdominant s-wave component at the interface is shown to robust against the impurity scattering while that for a subdominant d_{xy}-wave component is largely suppressed with the increase of the impurity scattering rate. The zero-bias conductance peak due to the zero-energy Andreev bound states is significantly broadened for the case of Born limit impurity compared with that of unitary limit impurity.

Recent extensive experimental and theoretical studies have revealed that the pair potentials of high-$T_{\rm c}$ superconductors have $d_{x^2-y^2}$-wave symmetry.[1–3,5]. One of the most remarkable differences of $d_{x^2-y^2}$-wave superconductors from conventional s-wave superconductors is the presence of internal phase of the pair potential. As for tunneling phenomena, the appearance of zero-bias conductance peak (ZBCP) in tunneling conductance at [110] surface of $d_{x^2-y^2}$-wave superconductors reflects the sign change of effective pair potential through the reflection of quasiparticle at the surface.[6,7] Qualitative features on the orientational dependence of the tunneling spectra in high-T_c superconductors have been experimentally checked by several groups and good consistencies have been obtained[8–12]. However, detailed line shape of the conductance spectra are not fully understood yet. For example, the ZBCP is expected to become δ-functional form for the high-barrier limit case based on the theoretical formula, while experimental spectra are largely broadened in usual cases and the origin of the broadening is still an open problem.

Possible explanations for the broadening are the interface roughness and the impurity scattering which may inevitably exist in the actual samples. Several existing theories clarified the influence of the diffuse scattering at the surface on the surface density of state[14–17] and on the Josephson current[18,19]. On the other hand, Poenicke, Barash, Bruder and Istyukov (PBBI theory) studied the influence of the bulk impurity on the surface density of states and Josephson current[20]. They discovered that the broadening of Andreev bound states due to unitary scattering is substantially weaker than that in Born limit scattering. Although PBBI theory clarified important aspects of the bulk impurity effect on the charge transport effect on the d-wave superconductor junctions, there still remain several open problems. One is the detailed dependence of the conductance spectra on transparency of the junction. In PBBI theory, only the junctions with low transparency limit is treated. However, transparency of the junctions in actual experiments is not restricted to this limit. Actually, it has been revealed by the previous theories that the line shape of the tunneling conductance strongly depends on the transparency of the junction[5,7,9]. The other is the effect of the bulk impurity on the local inducement of the subdominant pair potentials which break the time

reversal symmetry. This is important because recent theoretical and experimental study have shown the possibility that a subdominant s-wave component or d_{xy}-wave component is locally induced near the interface of $d_{x^2-y^2}$-wave superconductor[16,22–24]. On the other hand, the appearance of the predicted splitting of the ZBCP's has been detected only in several restricted experiments and conflicting results have been reported thus far[25,26,40]. Therefore it is an interesting topic to study the stability of the subdominant pair potential under the existence of bulk impurity.

In this paper, we will calculate the tunneling conductance in normal metal / insulator / $d_{x^2-y^2}$-wave ($n/I/d$) superconductor junctions using the quasiclassical formalism of unconventional superconductors. The self-energy is calculated in the framework of self-consistent t-matrix approximation. We concentrate on two limits, *i.e.* the limits of the Born scattering and the unitary scattering. For [100] oriented junction, the obtained tunneling conductance at zero bias voltage is enhanced (suppressed) for high (low) transparency of the junction. The degree of the enhancement (suppression) is much more significant for the unitary scattering case. While for [110] oriented junction, the broadening of the zero bias conductance peak (ZBCP) is much more significant for the Born scattering case[20]. We further study the situation where a subdominant s-wave component which breaks the time reversal symmetry is induced near the interface of d-wave superconductor. The subdominant s-wave component seems to be robust against the presence of the impurity scattering. While the subdominant d_{xy}-wave component is reduced drastically with the increase of the magnitude of the scattering rate of impurity.

The model examined here is a two-dimensional $n/I/d$ junction within the quasiclassical formalism[27,28] where the pair potential has a spatial dependence

$$\bar{\Delta}(x,\theta) = \begin{cases} 0, & (x \leq 0) \\ \bar{\Delta}_R(x,\theta), & (x \geq 0) \end{cases} \tag{1}$$

Here θ is the angle of quasiparticle trajectory measured from the x axis. If we apply this formula to d-wave superconductors including a subdominant s-wave and d_{xy}-wave component near the interface, $\bar{\Delta}_R(x,\theta)$ is decomposed into

$$\bar{\Delta}_R(x,\theta) = \Delta_d(x)\cos[2(\theta-\alpha)] + \Delta_s(x) + \Delta_{d'}(x)\sin[2(\theta-\alpha)] \tag{2}$$

where α denotes the angle between the normal to the interface and the x axis of the crystal. The insulator located between the normal metal and the superconductor is modeled by a δ function. The magnitude of the δ-function denoted as H determines the transparency of the junction σ_N, with $\sigma_N = 4\cos^2\theta/[Z^2 + 4\cos^2\theta]$ and $Z = 2mH/\hbar^2 k_F$. The effective mass m and Fermi momentum k_F are assumed to be constant throughout the junction. We solve the Eilenberger equation under the existence of bulk impurity in the superconductor[29,30]. The tunneling conductance is obtained thorough the coefficient of the Andreev and normal reflection[31–34]. In the following, we will concentrate on the normalized tunneling conductance $\sigma_T(eV)$[5,9]

$$\sigma_T(eV) = \frac{\int_{-\pi/2}^{\pi/2} d\theta \sigma_S(eV,\theta)\cos\theta}{\int_{-\pi/2}^{\pi/2} d\theta \sigma_N \cos\theta}. \tag{3}$$

$$\sigma_S(eV,\theta) = \sigma_N \frac{1 + \sigma_N \left|\eta_{R,+}(0,\theta)\right|^2 + (\sigma_N - 1)\left|\eta_{R,+}(0,\theta)\eta_{R,-}(0,\theta)\right|^2}{\left|1 + (\sigma_N - 1)\eta_{R,+}(0,\theta)\eta_{R,-}(0,\theta)\right|^2}. \tag{4}$$

Note that $\sigma_T(eV)$ is expressed only by $\eta_{R,\pm}(x,\theta)$ just at the boundary ($x = 0$) where $\eta_{R,\pm}(x,\theta)$ obeys the following equations[35],

$$\frac{d}{dx}\eta_{R,+}(x,\theta) = \frac{1}{i\hbar v_F \cos\theta}\left[-\Lambda_1(E,x,\theta_+)\eta_{R,+}^2(x,\theta) - \Lambda_2(E,x,\theta_+) + 2\Lambda_3(E,x,\theta)\eta_{R,+}(x,\theta)\right], \tag{5}$$

$$\frac{d}{dx}\eta_{R,-}(x,\theta) = \frac{1}{i\hbar v_F \cos\theta}\left[-\Lambda_2(E,x,\theta_-)\eta_{R,-}^2(x,\theta) - \Lambda_1(E,x,\theta_-) + 2\Lambda_3(E,x,\theta)\eta_{R,-}(x,\theta)\right], \tag{6}$$

$$\Lambda_1(E,x,\theta) = \bar{\Delta}_R(x,\theta_+) - a_1(E,x) + ia_2(E,x),$$

$$\Lambda_2(E,x,\theta) = \bar{\Delta}_R^*(x,\theta_+) + a_1(E,x) + ia_2(E,x),$$

$$\Lambda_3(E,x) = E - a_3(E,x) \tag{7}$$

with $E = eV$, $v_F = k_F/m$, $\theta_+ = \theta$ and $\theta_- = \pi - \theta$, and $\bar{\Delta}_R(x, \theta_+)$ $[\bar{\Delta}_R(x, \theta_-)]$ is the effective pair potential felt by an electron [a hole] like quasiparticle with an electron injection from the left normal metal. The quasiparticle energy E is measured from the Fermi energy.

The spatial dependence of the pair potentials are determined by the following equations[36]

$$\Delta_s(x) = g_s k_B T \sum_{\omega_n} \frac{1}{2\pi} \int_{-\pi/2}^{\pi/2} d\theta' \{[g_R(\theta', x)]_{12} - [g_R^+(\theta', x)]_{12}\} \tag{8}$$

$$\Delta_d(x) = g_d k_B T \sum_{\omega_n} \frac{1}{2\pi} \int_{-\pi/2}^{\pi/2} d\theta' \cos[2(\theta' - \alpha)] \{[g_R(\theta', x)]_{12} - [g_R^+(\theta', x)]_{12}\} \tag{9}$$

$$\Delta_{d'}(x) = g_{d'} k_B T \sum_{\omega_n} \frac{1}{2\pi} \int_{-\pi/2}^{\pi/2} d\theta' \sin[2(\theta' - \alpha)] \{[g_R(\theta', x)]_{12} - [g_R^+(\theta', x)]_{12}\} \tag{10}$$

$$\lim_{x\to\infty} \Delta_s(x) = 0, \ \lim_{x\to\infty} \Delta_d(x) = \Delta_0, \ \lim_{x\to\infty} \Delta_{d'}(x) = 0 \tag{11}$$

with dimensionless inter-electron coupling of the s-wave g_s, d_{xy}-wave $g_{d'}$ and $d_{x^2-y^2}$-wave g_d, respectively. The self-energy $a_i(E, x)$ $(i = 1, 3)$ describes the impurity scattering and is given by

$$a_i(i\omega_n, x) = \frac{\frac{\hbar}{2\tau} \frac{< g_i(\theta, x) >}{1-\sigma}}{1 - \frac{\sigma}{1-\sigma} \sum_i < g_i(\theta, x) >^2} \tag{12}$$

$$\hat{g}_R(\theta, x) = g_1(\theta, x)\hat{\tau}_1 + g_2(\theta, x)\hat{\tau}_2 + g_3(\theta, x)\hat{\tau}_3$$

with $\omega_n = 2\pi k_B T(n + 1/2)$. In the above, $\hat{\tau}_i$ denotes the Pauli matrix and $< \ldots >$ means the average over the Fermi surface. Here $\hbar/(2\tau)$ denotes the normal scattering rate, while σ measures the strength of a simple impurity potential. The spatial dependence of the quasiclassical Green's function $\hat{g}_R(\theta, x)$ is determined by[36]

$$\hat{g}_R(\theta, x) = U_R(\theta, x, 0)\hat{g}_R(\theta, 0)U_R^{-1}(\theta, x, 0) \tag{13}$$

$$i\hbar v_{Fx} \frac{\partial}{\partial x} U_R(\theta, x, 0) = - \begin{pmatrix} \Lambda_3(i\omega_n, x) & \Lambda_1(i\omega_n, x, \theta_+) \\ -\Lambda_2(i\omega_n, x, \theta_+) & -\Lambda_3(i\omega_n, x) \end{pmatrix} U_R(\theta, x, 0), \tag{14}$$

with $U_R(\theta,0,0)=1$. In the actual numerical calculations, $\eta_{R,\pm}(x,\theta)$ is calculated from Eqs. (5) to (6). Since $\hat{g}_R(\theta,0)$ is expressed by $\eta_{R,\pm}(\theta,0)$, $\hat{g}_R(\theta,x)$ is obtained using Eqs. (13) to (14). Subsequently, the spatial dependence of the pair potentials $\Delta_d(x)$, $\Delta_{d'}(x)$ and $\Delta_s(x)$ are calculated by Eqs. (8) to (11). The self-energies $a_i(i\omega_n,x)$ are calculated by Eq. (12). To get self-consistently determined pair potentials and self-energies due to the impurity scattering this process is repeated until enough convergence is obtained. In the following calculation, the two important parameters characterizing the impurity scattering are $\frac{\hbar}{2\tau\Delta_{c0}}$ and σ where Δ_{c0} denotes the magnitude of the bulk pair potential without the existence of impurity scattering. The magnitude of Δ_0 depends on $\frac{\hbar}{2\tau\Delta_{c0}}$ and σ.

First, let us consider the case where neither $\Delta_s(x)$ nor $\Delta_{d'}(x)$ present. One of the typical example is the [100] oriented junction, *i.e.*, $\alpha=0$ case, where both the transmitted electron like and hole like quasiparticle feel the same sign of the pair potentials. For high transparent junctions *i.e.* $Z=0$ [see Fig. 1(a)], only the Andreev scattering takes place at the interface and the resulting conductance shows zero-bias enhancement due to the Andreev reflction without impurity. With the introduction of the impurity scattering the height of the peak is suppressed. The degree of this suppression is much more significant for unitary scattering case [see curve *c* in Fig. 1 (a)]. On the other hand, for larger magnitude of Z [see Fig. 1(b)], $\sigma_T(eV)$ has a gap like structure without impurity. The magnitude of $\sigma_T(0)$ is enhanced with the increase of Z. The degree of this enhancement is much more significant in the unitary scattering case. In order to understand these line shapes of the tunneling conductances, we will look at $eV=0$, where $\eta_{R,\pm}(0,\theta)=\pm i$ is satisfied without impurity scattering. With the introduction of impurity potential, the magnitude of $\eta_{R,\pm}(0,\theta)$ is suppressed and we can denote $\eta_{R,\pm}(0,\theta)=\pm i\exp(-\gamma_0)$. Here, γ_0 is a function with positive value and enhances with the increase of the magnitude of $a_3(0,0)$, *i.e.*, the magnitude of $\frac{\hbar}{2\tau\Delta_{c0}}$. For $\alpha=0$, since $\eta_R(0,\theta_+)=\pm i\exp(-\gamma_0)$ and $\eta_R(0,\theta_-)=\pm i\exp(-\gamma_0)$ are satisfied, the resulting $\bar{\sigma}_S(0,\theta)$ is $[1+\exp(-2\gamma_0)]$ and $[1-\exp(-2\gamma_0)]/[1+\exp(-2\gamma_0)]$ for $Z=0$ and sufficiently larger magnitude of Z, respectively. Since the magnitude of $a_3(0,0)$ is enhanced for the unitary scattering case, the resulting γ_0 also enhances. Consequently, the magnitude of $\bar{\sigma}_S(0,\theta)$ is

much more enhanced for the Born scattering case for $Z = 0$, while the opposite situation happens for sufficiently larger value of Z.

Next, let us look at the $\alpha = \pi/4$ case, where $\sigma_T(eV)$ has a zero bias conductance peak (ZBCP) with small magnitude of σ_N[7–9]. For $Z = 0$, almost the same result as that in Fig. 1(a) is obtained. This is because well defined bound states do not exist in the absence of the barrier potential. With the increase of the magnitude of Z, the ZBCP shows up due to Andreev bound state formation without impurity[7–9]. As shown in Fig. 2, the height of the ZBCP is suppressed with the introduction of the impurity scattering. In the Born limit (see curve b in Fig. 2), the reduction of the amplitude of the peak height and the broadening of the peak width is most significant. To understand this feature, here, we focus on $eV = 0$, where $\eta_{R,+}(0,\theta) = i\exp(-\gamma_0)$ and $\eta_{R,-}(0,\theta) = -i\exp(-\gamma_0)$ are satisfied. The resulting $\bar{\sigma}_S(0,\theta)$ is $[1+\exp(-2\gamma_0)]/[1-\exp(-2\gamma_0)]$ for sufficiently large magnitude of Z. It should be remarked that the magnitude of $a_3(0,0)$ is much more enhanced for Born scattering case due to the formation Andreev bound state at the interface[20] and the resulting γ_0 is much more enhanced. Consequently, the amplitude of $\bar{\sigma}_S(0,\theta)$, and $\sigma_T(0)$ in the unitary limit is larger than that in the Born limit.

In Fig. 3, the width of ZBCP W is plotted as a function of scattering rate $\hbar/(2\tau\Delta_{c0})$ in the Born limit. For small value of Z, W is insensitive with the increase of $\hbar/(2\tau\Delta_{c0})$. However, with the increase of the amplitude of Z, W becomes a monotonically increasing function of $\hbar/(2\tau\Delta_{c0})$. For sufficiently larger value of Z, W is roughly proportional to the inverse of $\sqrt{\hbar/(2\tau\Delta_{c0})}$ as predicted by PBBI theory[20].

Under the presence of the ZBCP, since the quasiparticle density of states at the zero energy near the interface are enhanced, a subdominant s-wave (d_{xy}-wave) component of the pair potential $\Delta_s(x)$ ($\Delta_{d'}(x)$) can be induced near the interface, when a finite s-wave (d_{xy}-wave) pairing interaction strength exists, even though the bulk symmetry remains pure $d_{x^2-y^2}$-wave[16,22–25]. Since the phase difference of the $d_{x^2-y^2}$-wave and s-wave components is not always a multiple of π, the mixed state breaks the time-reversal symmetry[16,24]. It is an interesting problem to clarify the stability of this broken time reversal symmetry state

(BTRSS). Here, we study two cases; (a) a subdominant s-wave component is induced near the interface, *i.e.*, $\Delta_s(x) \neq 0$, $\Delta_{d'}(x) = 0$ [see Fig. 4(a)], (b) a subdominant d_{xy}-wave component is induced near the interface, *i.e.*, $\Delta_{d'}(x) \neq 0$, $\Delta_s(x) = 0$ [see Fig. 4(b)]. Here, the transition temperature of the s-wave component alone T_s and that of d_{xy}-wave component $T_{d'}$ are chosen as $T_s = 0.3T_d$ and $T_{d'} = 0.3T_d$, where T_d is the transition temperature of $d_{x^2-y^2}$ pair potential without any other components. The transition temperature T_s, $T_{d'}$ and T_d directly correspond to the magnitude of attractive inter-electron coupling g_s, $g_{d'}$ and g_d, respectively. In Fig. 4, the relative magnitude of the subdominant s-wave or d_{xy} component at the interface, *i.e.*, $\mid \mathrm{Imag}\Delta_s(0) \mid /\Delta_0$ or $\mid \mathrm{Imag}\Delta_{d'}(0) \mid /\Delta_0$ is plotted as a function of $\hbar/(2\tau\Delta_{c0})$ both in the Born and unitary limit. The magnitude of $\mid \mathrm{Imag}\Delta_s(0) \mid /\Delta_0$ is insensitive with the change of the value of $\hbar/(2\tau\Delta_{c0})$, while that for $\mid \mathrm{Imag}\Delta_{d'}(0) \mid /\Delta_0$ is reduced with the increase of the magnitude of $\frac{\hbar}{2\tau\Delta_{c0}}$. The resulting $\sigma_T(eV)$ is plotted in Fig. 5 for $\frac{\hbar}{2\tau\Delta_{c0}} = 0.1$ both in the Born limit and unitary scattering case. In the case where subdominant s-wave component is induced at the interface, the resulting $\sigma_T(eV)$ has a ZBCP splitting independent of the introduction of the impurity scattering. On the other hand, the ZBCP is recovered with the introduction of impurity scattering when subdominant pairing is d_{xy}-wave (see Fig. 5(b)). In this case, the onset of the ZBCP splitting depends on the magnitude of $\frac{\hbar}{2\tau\Delta_{c0}}$. From these behaviors, we can distinguish the symmetry of the subdominant pair potential.

In this paper, tunneling conductance between normal metal / d-wave superconductor junctions is studied under the presence of bulk impurities in superconductors. We use quasiclassical theory and include impurity scattering by t-matrix approximation, and the spatial variation of the pair potentials and self-energy are determined self-consistently. For [100] oriented junction, obtained tunneling conductance at zero bias voltage is enhanced (suppressed) for high (low) transparency of the junction. The degree of the enhancement (suppression) is much more significant for the unitary scattering case. While for [110] oriented low transparent junctions, the broadening of the zero bias conductance peak (ZBCP) is much more significant for the Born scattering case[20]. We further study the situation

where a subdominant component which breaks the time reversal symmetry is induced near the interface of d-wave superconductor[16,22–25]. The subdominant s-wave component is robust against the introduction of the impurity scattering. While the subdominant d_{xy}-wave component is reduced drastically with the increase of the magnitude of the scattering rate of impurity. We will comment on the relation between present results with experimental ones. In the cases of high-T_c superconductors, impurities intrinsically exist in real samples. For example, the enhancement of zero-bias conductance is reported in c-axis observation of STM experiments[37]. We believe that the observed features (especially the enhancement of conductance) in this experiment are consistent with the result for the Born limit case. On the other hand, in the cases of in-plane tunneling, only a few papers reported the splitting of ZBCP in YBCO junctions[25,40] and the others report the absence of the splitting (for example,[26]). If the appearance and disappearance of the splitting is simply determined by the Born impurity concentration in samples, the promising subdominant component is concluded to be d_{xy}-wave. However, from the microscopic calculation using the $t-J$ model, the subdominant d_{xy}-wave is hard to be realized while the subdominant s-wave component is much more plausible[38,39]. In this sence, we should perform the tunneling experiments with controlled impurity inclusion in the high-T_c cuprates. Also we must reveal the origin of the attractive potential which induces subdominant d_{xy}-wave component in order to overcome this contradiction. Furthermore, it should be pointed out that the magnetically active interface also induces the ZBCP splitting[41,42]. To resolve the origin of the ZBCP splitting in the actual junctions, we must study much more about microscopic electronic properties about the interface of high-T_c cuprates.

Throughout this paper, the roughness of the interface is not taken into account. Since the roughness of the interface suppresses the magnitude of the ZBCP[15], the low voltage behavior of the $\sigma_T(eV)$ is also expected to be influenced. It is an interesting future problem to calculate $\sigma_T(eV)$ both under the existence of surface roughness and the bulk impurity. In the present paper, the effect of bulk impurity is studied where the spatial dependence of τ is not taken into account. In the actual sample, it is expected that the value of τ near

the interface is much more smaller than that in the bulk. The influence of Andreev bound state on the Josephson effect in d-wave superconductors is also an interesting issue[18,20,43,44]. To resolve the bulk impurity effect on the Josephson current in the junctions with sufficient transparency is an interesting future problem since the experimentally accessible junction is not always in the tunneling limit[45].

This work was partially supported by a Grant-in-aid for Scientific Research from the Ministry of Education, Science, Sports and Culture.

REFERENCES

[1] D.J. Scalapino, Physics Report. **250**, 329 (1995).

[2] D. J. Van Harlingen, Rev. Mod. Phys. **67**, (1995) 515.

[3] C. C. Tsuei and J. R. Kirtley, Rev. Mod. Phys. **72**, 969 (2000).

[4] M. Sigrist and T.M. Rice, Rev. Mod. Phys. **67** 503 (1995).

[5] S. Kashiwaya and Y. Tanaka, Rep. Prog. Phys. **63**, 1641 (2000).

[6] C.R. Hu, Phys. Rev. Lett. **72**, 1526 (1994).

[7] Y. Tanaka and S. Kashiwaya, Phys. Rev. Lett. **74**, 3451 (1995).

[8] S. Kashiwaya, *et. al*. Phys. Rev. B **51**, 1350 (1995).

[9] S. Kashiwaya, Y. Tanaka, M. Koyanagi, and K. Kajimura, Phys. Rev. B **53**, 2667 (1996).

[10] J. Y. T. Wei, N.-C. Yeh, D. F. Garrigus, and M. Strasik, Phys. Rev. Lett. **81**, 2542 (1998).

[11] W. Wang, M. Yamazaki, K. Lee, and I. Iguchi, Phys. Rev. B **68**, 4272 (1999).

[12] I. Iguchi, W. Wang, M. Yamazaki, Y. Tanaka and S. Kashiwaya, Phys. Rev. B **62** R6131 (2000).

[13] M. B. Walker and P. Pairor, Phys. Rev. B **59** 1421 (1999), *ibid*., **60** 10395 (1999).

[14] M. Matsumoto and H. Shiba, J. Phys. Soc. Jpn., **64**, 1703 (1995).

[15] K. Yamada, *et al*., J. Phys. Soc. Jpn **65**, 1540 (1996).

[16] M. Fogelström, D. Rainer, and J.A. Sauls, Phys. Rev. Lett. **79**, 281 (1997).

[17] Y. S. Barash, A. A. Svidzinsky and H. Burkhardt, Phys. Rev. B **55**, 15282 (1997).

[18] Yu. S. Barash, H. Burkhardt, and D. Rainer, Phys. Rev. Lett. **77**, 4070 (1996).

[19] Y. Tanaka and S. Kashiwaya, Physica C **317-318**, 403 (1999).

[20] A. Poenicke, Yu. S. Barash, C. Bruder, and V. Istyukov, Phys. Rev. B **59**, 7102 (1999).

[21] L. J. Buchholtz, M. Palumbo, D. Rainer and J.A. Sauls, J. Low. Temp. Phys. **101**, 1097 (1995).

[22] M. Sigrist, D.B. Bailey, R.B. Laughlin, Phys. Rev. Lett. **74**, 3249 (1995).

[23] K. Kuboki and M. Sigrist, J. Phys. Soc. Jpn, **65**, 361 (1996).

[24] M. Matsumoto and H. Shiba, J. Phys. Soc. Jpn., **64**, 4867 (1995).

[25] M. Covington, et al, Phys. Rev. Lett. **79**, 277 (1997).

[26] A. Sawa, et al., Physica C to be published: S. Kashiwaya, et al. in preparation.

[27] C. Bruder, Phys. Rev. B **41**, 4017 (1990).

[28] A. Millis, D. Rainer and J. A. Sauls, Phys. Rev. B **38**, 4504 (1988).

[29] G. Eilenberger, Z. Phys. **214** (1968) 195.

[30] J. W. Serene and D. Rainer, Phys. Rep. **101** 221 (1983).

[31] A. F. Andreev, Zh. Eksp. Teor. Fiz. **46**, 1823 (1964) [Sov. Phys. JETP **19**, 1228 (1964)].

[32] G.E. Blonder, M. Tinkham and T.M. Klapwijk, Phys. Rev. B **25**, 4515 (1982).

[33] A. V. Zaitsev, Zh. Eksp. Teor. Fiz. **86** 1745 (1984) [Sov. Phys. JETP **59**, 1015 (1984)].

[34] A.L. Shelankov, J. Low Temp. Phys. **60** 29 (1985).

[35] Y. Nagato, K. Nagai and J. Hara, J. Low Temp. Phys. **93**, 33 (1993).

[36] M. Ashida, S. Aoyama, J. Hara and K. Nagai, Phys. Rev. B **40**, 8673 (1989).

[37] E. W. Hudson, et. al., Science **285**, 88 (1999). For the unitary limit case, the see Zn impurity case: Pan, et. al, Nature **403** 746 (2000).

[38] Y. Tanuma, Y. Tanaka, M. Ogata and S. Kashiwaya, J. Phys. Soc. Jpn. **67** 1118 (1998).

[39] Y. Tanuma, Y. Tanaka, M. Ogata and S. Kashiwaya, Phys. Rev. B **60** 9817 (1999).

[40] R. Krupke and G. Deutscher, Phys. Rev. Lett. **83**, 4634 (2000).

[41] S. Kashiwayua, Y. Tanaka, N. Yoshida, and M. Beasley, Phys. Rev. B **60** 3572 (1999).

[42] J. X. Zhu, B. Friedman and C. S. Ting, Phys. Rev. B **59** 9558 (1999).

[43] Y. Tanaka and S. Kashiwaya, Phys. Rev. B **53**, 11957 (1996).

[44] Y. Tanaka and S. Kashiwaya, Phys. Rev. B **56**, 892 (1997).

[45] H. Arie, *et al*, Phys. Rev. B **62** (2000).

Figure Captions

Fig. 1. $\sigma_T(eV)$ for $n/I/d$ junction with $\alpha = 0$. (a) $Z = 0$, (b)$Z = 5$. a: clean lmit, $\frac{\hbar}{2\tau\Delta_{c0}} = 0$, b: Born limit, $\frac{\hbar}{2\tau\Delta_{c0}} = 0.1$, $\sigma = 0$, c: almost unitary limit, $\frac{\hbar}{2\tau\Delta_{c0}} = 0.1$, $\sigma = 0.99$.

Fig. 2. $\sigma_T(eV)$ for $n/I/d$ junction with $\alpha = \pi/4$ and $Z = 5$. a: clean lmit, $\frac{\hbar}{2\tau\Delta_{c0}} = 0$, b: Born limit, $\frac{\hbar}{2\tau\Delta_{c0}} = 0.1$, $\sigma = 0$, c: almost unitary limit, $\frac{\hbar}{2\tau\Delta_{c0}} = 0.1$, $\sigma = 0.99$.

Fig. 3. The width of ZBCP W/Δ_{c0} for $n/I/d$ junction with $\alpha = \pi/4$ is plotted as a function of $\frac{\hbar}{2\tau\Delta_{c0}}$. a: $Z = 1$, b:$Z = 5$, and c: $Z = 20$.

Fig. 4. The relative amplitude of the pair potential of a subdominant s-wave component and d_{xy}-wave component for $n/I/d$ junction with $\alpha = \pi/4$ and $Z = 5$ is plotted as a function of scattering strength of the impurity $\frac{\hbar}{2\tau\Delta_{c0}}$. (a) subdominant s-wave component, $\mid \mathrm{Imag}\Delta_s(0) \mid /\Delta_0$. (b) subdominant d_{xy}-wave component, $\mid \mathrm{Imag}\Delta_{d'}(0) \mid /\Delta_0$. a: Born limit, $\sigma = 0$, b: almost unitary limit, $\sigma = 0.99$.

Fig. 5. $\sigma_T(eV)$ for $n/I/d$ junction with $\alpha = \pi/4$ and $Z = 5$ under the existence of a subdominant s-wave component [(a)] and d_{xy}-wave component [(b)]. a: clean lmit, $\frac{\hbar}{2\tau\Delta_{c0}} = 0$, b: Born limit, $\frac{\hbar}{2\tau\Delta_{c0}} = 0.1$, $\sigma = 0$, c: almost unitary limit, $\frac{\hbar}{2\tau\Delta_{c0}} = 0.1$, $\sigma = 0.99$.

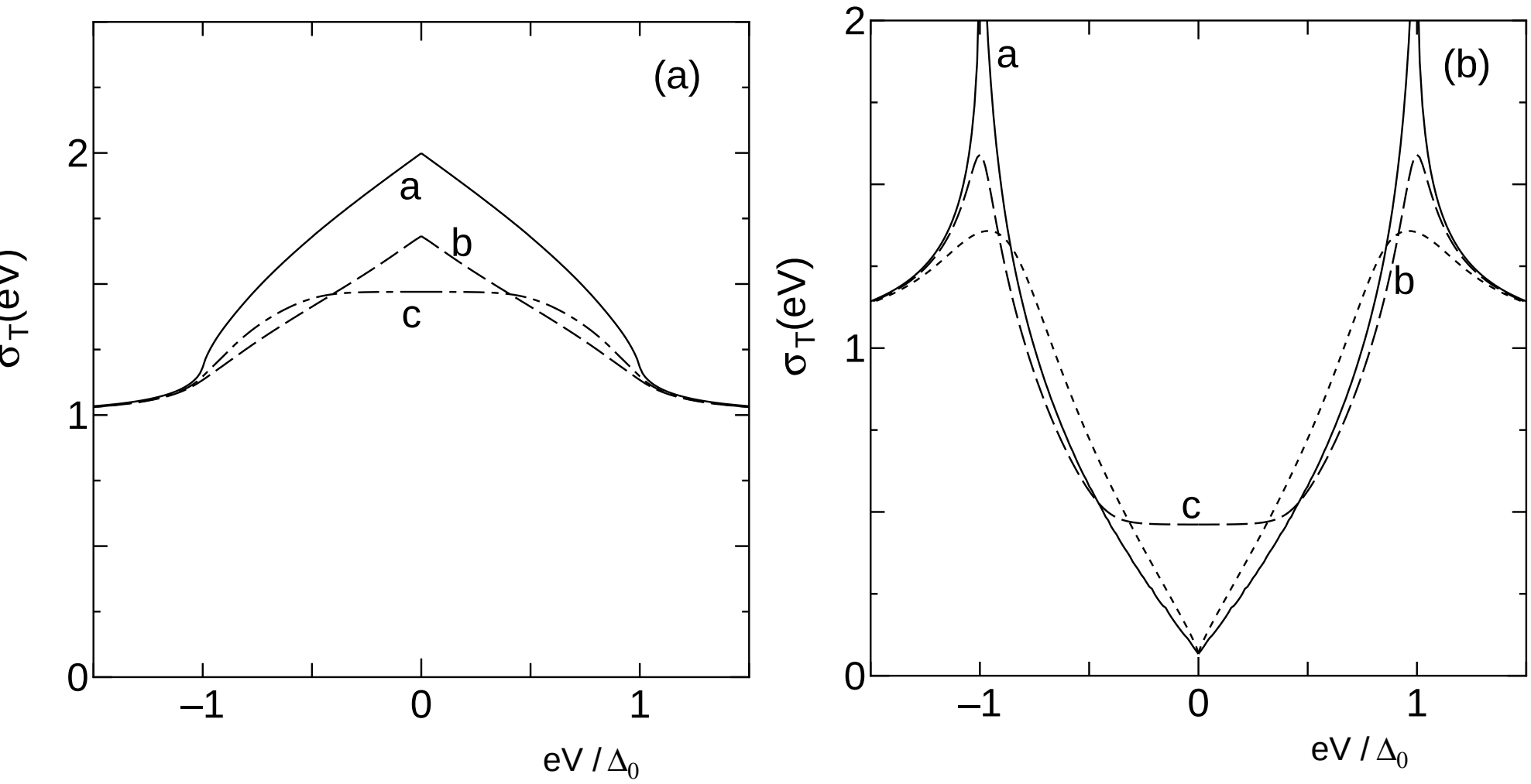


Fig. 1

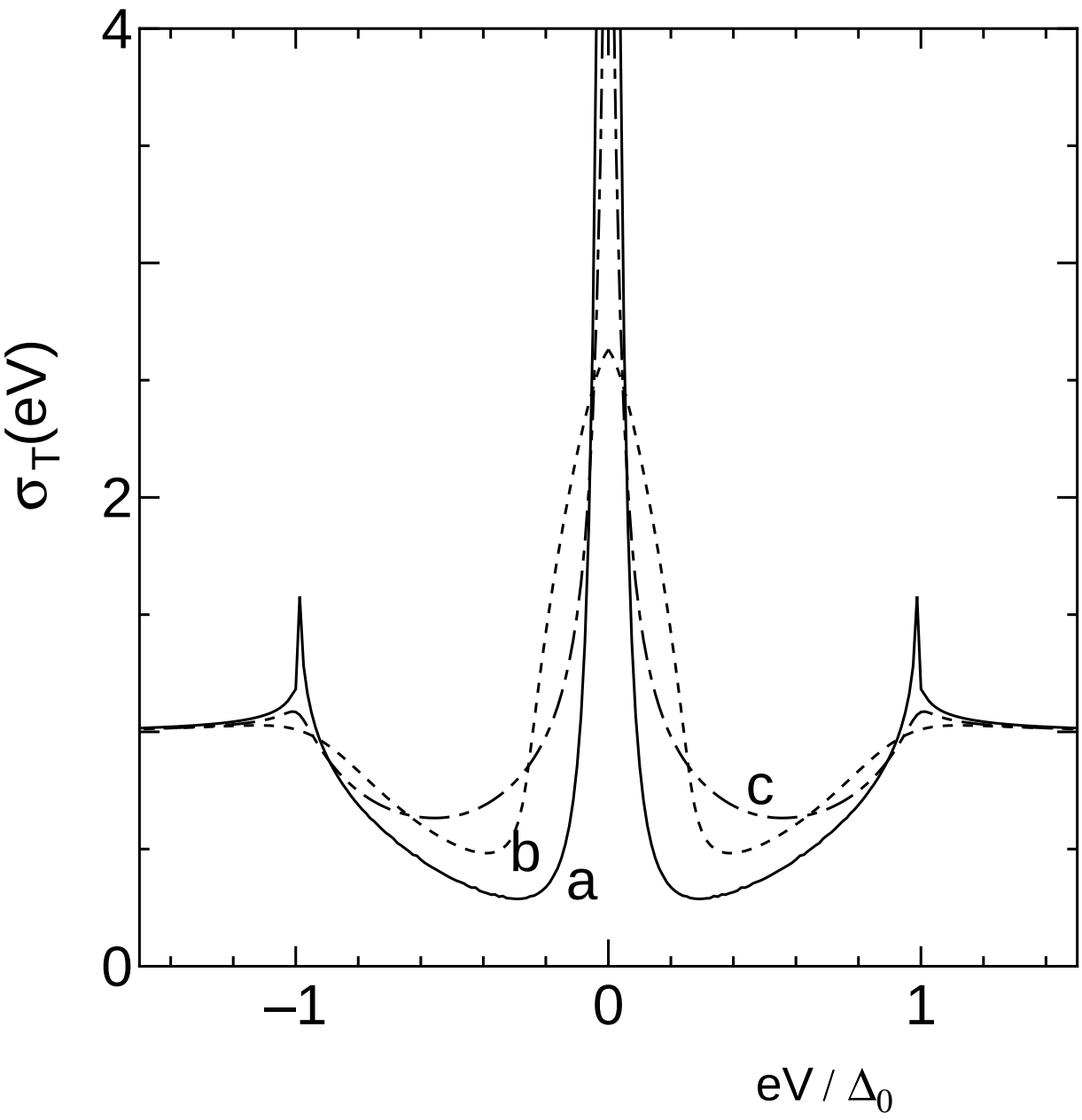


Fig. 2

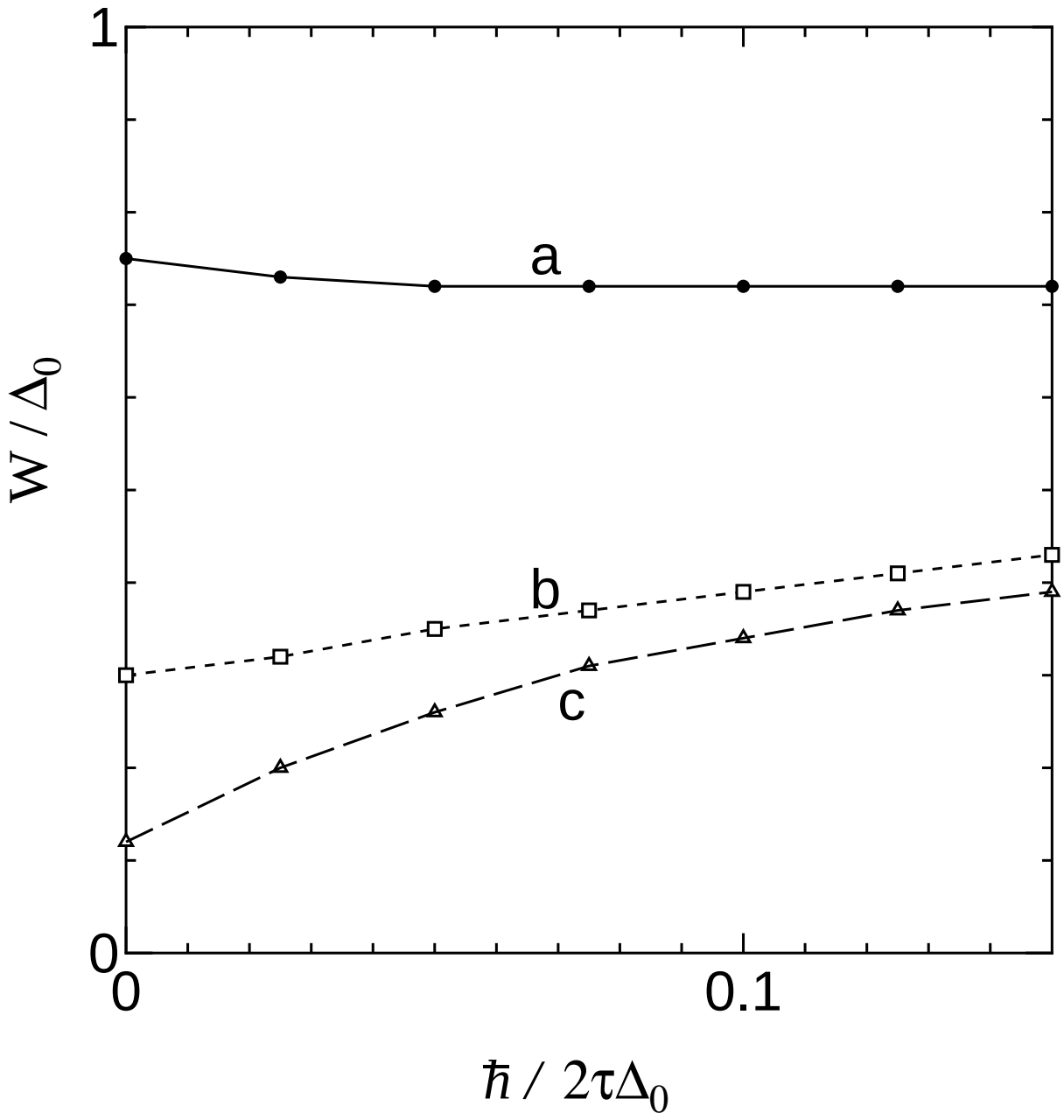
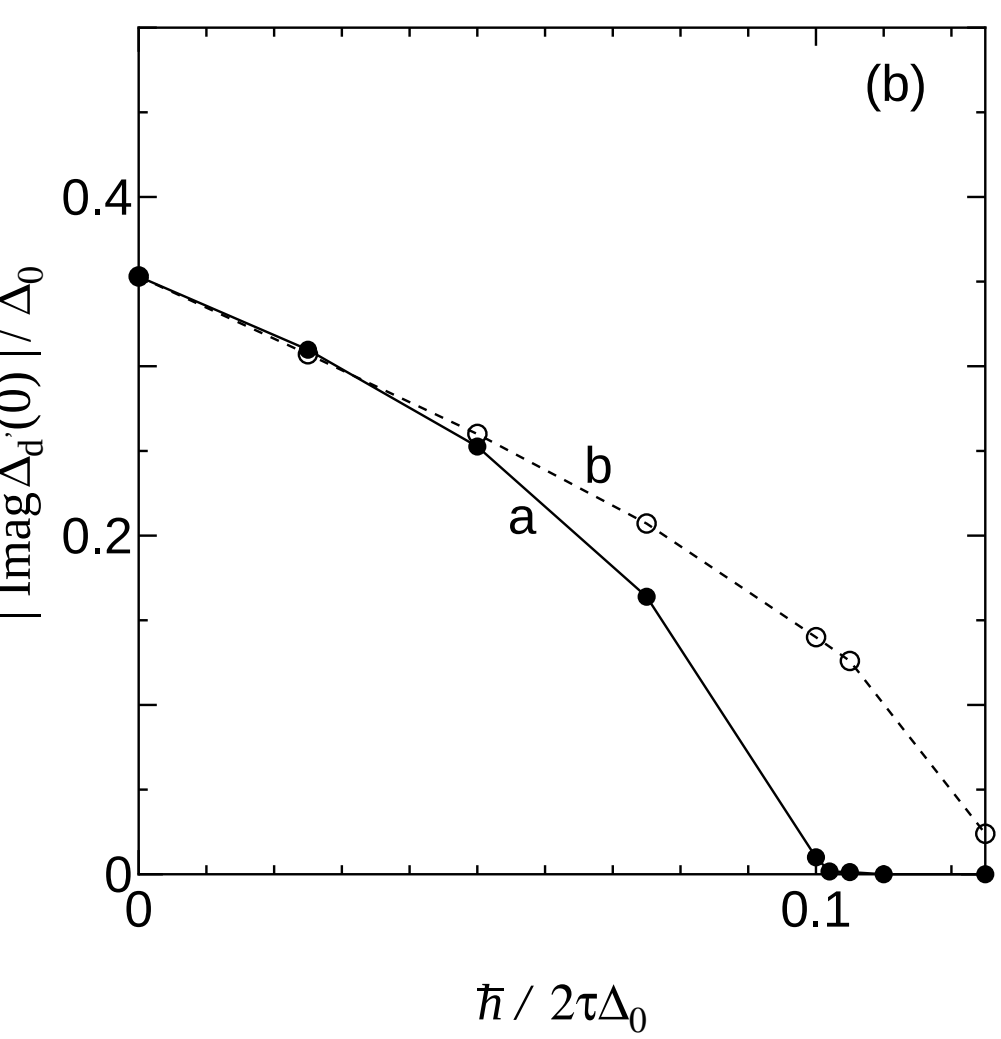


Fig. 3


(b)
0.4
0.2
0
0
0.1
| Imag $\Delta_{d'}(0)$ | / Δ_0
$\hbar$ / $2\tau\Delta_0$
a
b

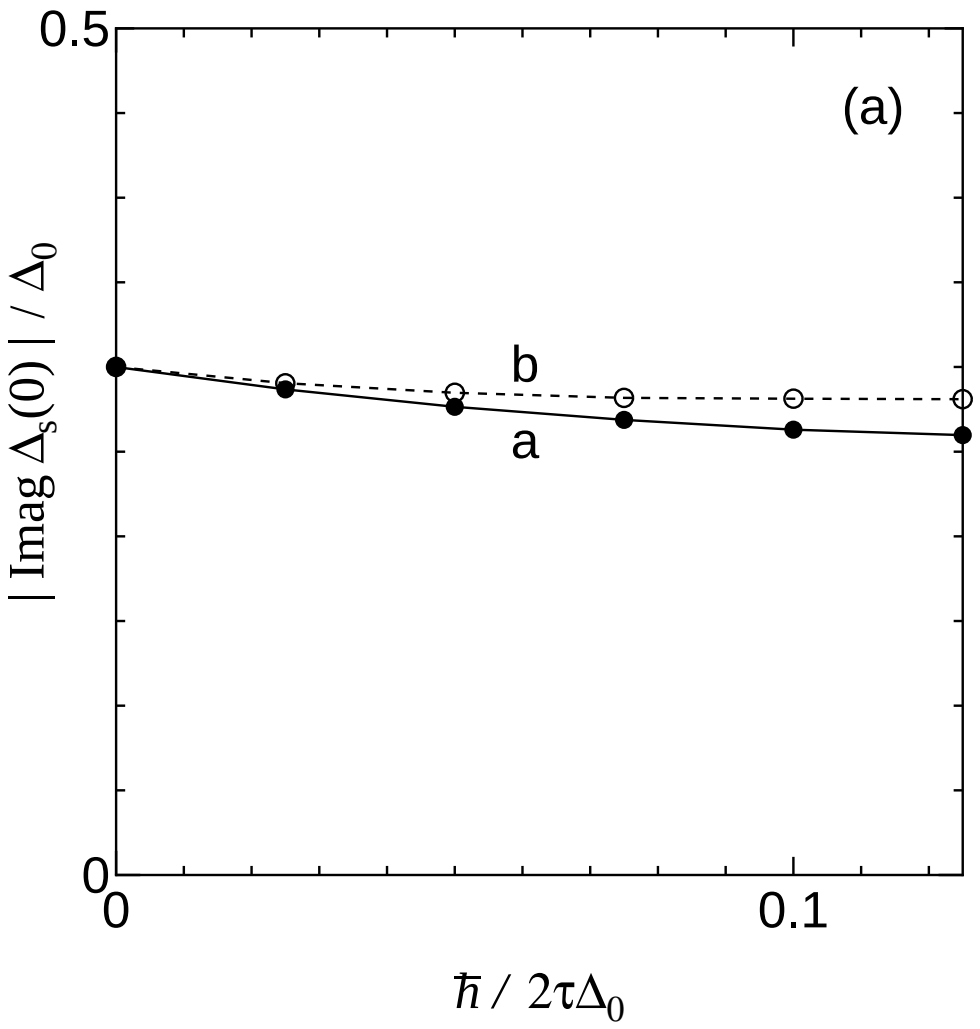

(a)
0.5
0
0
0.1
| Imag $\Delta_s(0)$ | / Δ_0
$\hbar$ / $2\tau\Delta_0$
a
b

Fig. 4

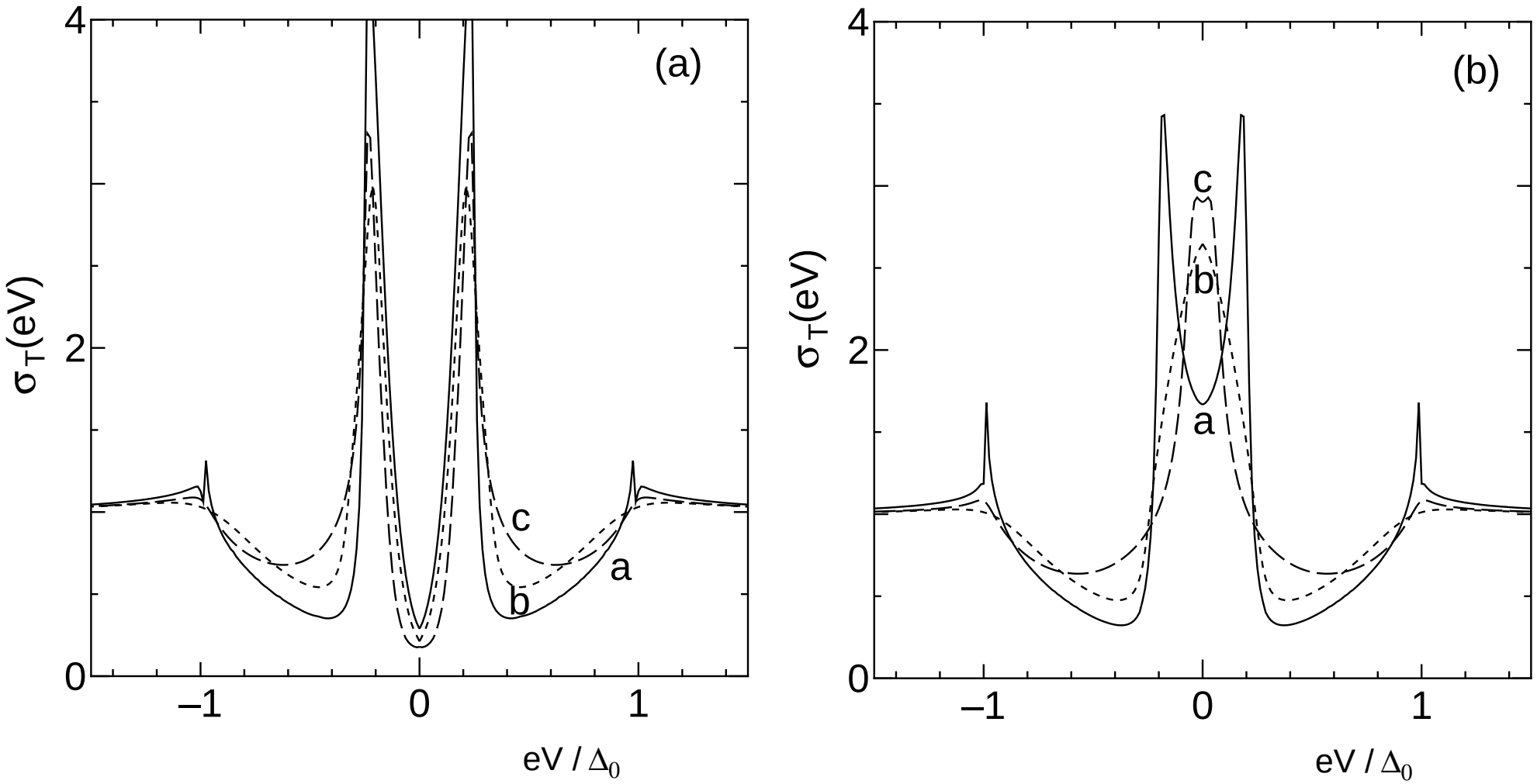


Fig. 5